



Product data sheet

1. General description

Ultrafast power diode in a SMB surface-mountable plastic package.

2. Features and benefits

- Low on-state loss
- Low leakage current
- Low thermal resistance
- Surface-mountable package
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Buck and Boost converter
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- Inverter freewheeling and protection diode

4. Quick reference data

uick reference data						
Parameter	Conditions		Values			Unit
e maximum rating						
repetitive peak reverse voltage			600		V	
average forward current	δ = 0.5 ; square-wave pulse; T _{lead} ≤ 105 °C; Fig. 1; Fig. 2; Fig. 3		3		A	
repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{lead} ≤ 105 °C; square-wave pulse		6		A	
non-repetitive peak forward current	$t_{\rm p}$ = 10 ms; $T_{\rm j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100			A	
	$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse;	110				А
Parameter	Conditions		Min	Тур	Max	Unit
aracteristics						
forward voltage	I _F = 3 A; T _j = 25 °C; <u>Fig. 6</u>		-	-	1.3	V
	I _F = 3 A; T _j = 150 °C; <u>Fig. 6</u>		-	0.88	1.05	V
characteristics		1	1	1	1	
reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 50 A/μs; T _i = 25 °C; <u>Fig. 7</u>		-	50	-	ns
	 maximum rating repetitive peak reverse voltage average forward current repetitive peak forward current non-repetitive peak forward current Parameter aracteristics forward voltage characteristics 	ParameterConditionsmaximum ratingrepetitive peak reverse voltageaverage forward current $\delta = 0.5$; square-wave pulse; $T_{lead} \le 105 ^{\circ}$ C; Fig. 1; Fig. 2; Fig. 3repetitive peak forward current $\delta = 0.5$; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $\delta = 0.5$; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $t_p = 10 \text{ms}$; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse; Fig. 4 $t_p = 8.3 \text{ms}$; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse;ParameterConditionsaracteristics $I_F = 3 \text{A}$; $T_j = 25 ^{\circ}$ C; Fig. 6 $I_F = 3 \text{A}$; $T_j = 150 ^{\circ}$ C; Fig. 6forward voltage $I_F = 3 \text{A}$; $T_j = 150 ^{\circ}$ C; Fig. 6there is the server of the serv	ParameterConditionsmaximum ratingrepetitive peak reverse voltage $\delta = 0.5$; square-wave pulse; $T_{lead} \le 105 ^{\circ}$ C; Fig. 1; Fig. 2; Fig. 3average forward current $\delta = 0.5$; square-wave pulse; $T_{lead} \le 105 ^{\circ}$ C; Fig. 1; Fig. 2; Fig. 3repetitive peak forward current $\delta = 0.5$; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $\delta = 0.5$; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $t_p = 10 \mathrm{ms}$; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse; Fig. 4 $t_p = 8.3 \mathrm{ms}$; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse;ParameterConditionsaracteristicsI_F = 3 A; T_j = 25 ^{\circ}C; Fig. 6 I_F = 3 A; T_j = 150 ^{\circ}C; Fig. 6characteristicsI_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/\mus;	ParameterConditionsValmaximum ratingrepetitive peak reverse voltage $\delta = 0.5$; square-wave pulse; $T_{iead} \le 105 \text{ °C}$; Fig. 1; Fig. 2; Fig. 36average forward current $\delta = 0.5$; square-wave pulse; $T_{iead} \le 105 \text{ °C}$; Fig. 1; Fig. 2; Fig. 37repetitive peak forward current $\delta = 0.5$; $t_p = 25 \ \mu s$; $T_{iead} \le 105 \text{ °C}$; square-wave pulse1non-repetitive peak forward current $\delta = 0.5$; $t_p = 25 \ \mu s$; $T_{iead} \le 105 \text{ °C}$; square-wave pulse1non-repetitive peak forward current $t_p = 10 \ m s$; $T_{j(init)} = 25 \ ^{\circ}C$; sine-wave pulse; Fig. 41 ParameterConditionsMinaracteristics I I_F = 3 A; T_j = 25 \ ^{\circ}C; Fig. 6-forward voltageI_F = 3 A; T_j = 25 \ ^{\circ}C; Fig. 6-I_F = 3 A; T_j = 150 \ ^{\circ}C; Fig. 6 characteristics I I_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/\mus;-	ParameterConditionsValuese maximum ratingrepetitive peak reverse voltage 600 average forward current $\delta = 0.5$; square-wave pulse; $T_{lead} \le 105$ °C; Fig. 1; Fig. 2; Fig. 3 600 average forward current $\delta = 0.5$; square-wave pulse; $T_{lead} \le 105$ °C; square-wave pulse 3 repetitive peak forward current $\delta = 0.5$; $t_p = 25 \ \mu s$; $T_{lead} \le 105$ °C; square-wave pulse 6 non-repetitive peak forward current $t_p = 10 \ ms$; $T_{j(init)} = 25 \ ^{\circ}C$; sine-wave pulse; $Fig. 4$ 100 ParameterConditionsMinTyparacteristics $I_F = 3 \ A$; $T_j = 25 \ ^{\circ}C$; Fig. 6 $ -$ forward voltage $I_F = 3 \ A$; $T_j = 150 \ ^{\circ}C$; Fig. 6 $ -$ there is the second pulse $I_F = 3 \ A$; $T_j = 150 \ ^{\circ}C$; Fig. 6 $ 0.88$ characteristicsreverse recovery time $I_F = 1 \ A$; $V_R = 30 \ V$; $dI_F/dt = 50 \ A/\mu$ s; $ 50$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Values \\ \hline maximum rating \\ \hline repetitive peak reverse voltage & 600 \\ \hline average forward current & $\delta = 0.5$; square-wave pulse; $T_{lead} \le 105 ^{\circ}C$; $$ 3 \\ \hline repetitive peak forward current & $\delta = 0.5$; t_p = 25 μ; $T_{lead} \le 105 ^{\circ}C$; $$ 6 \\ \hline current & $\delta = 0.5$; t_p = 25 μ; $T_{lead} \le 105 ^{\circ}C$; $$ 6 \\ \hline current & $t_p = 10$ ms; $T_{j(nit)} = 25 ^{\circ}C$; sine-wave pulse; $$ 100 \\ \hline repetitive peak forward current & $t_p = 10$ ms; $T_{j(nit)} = 25 ^{\circ}C$; sine-wave pulse; $$ 100 \\ \hline example & $t_p = 8.3$ ms; $T_{j(nit)} = 25 ^{\circ}C$; sine-wave pulse; $$ 110 \\ \hline example & $t_p = 3$ A$; $T_j = 25 ^{\circ}C$; $fig. 6$ $$ $-$ $$ $-$ $$ 1.3 \\ \hline reverse recovery time $$ $I_F = 1$ A; $V_R = 30$ V; $dI_F/dt = 50$ $A/$\mu$; $$ $-$ 50 $$ $-$ $ $$ 50 $$ $-$ $$ $$ 50 $$ $-$ $$ $$ 50 $$ $-$ $$ $$ 50 $$ $-$ $$ $$ $$ 50 $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$

5. Pinning information

Simplified outline	Graphic symbol
1 2	К <u>— А</u> 001ааа020

6. Ordering information

Table 3. Ordering information							
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date	
MURS360B	SMB	MURS360BJ	Reel	3000	SMB	20-Feb-2017	

7. Marking

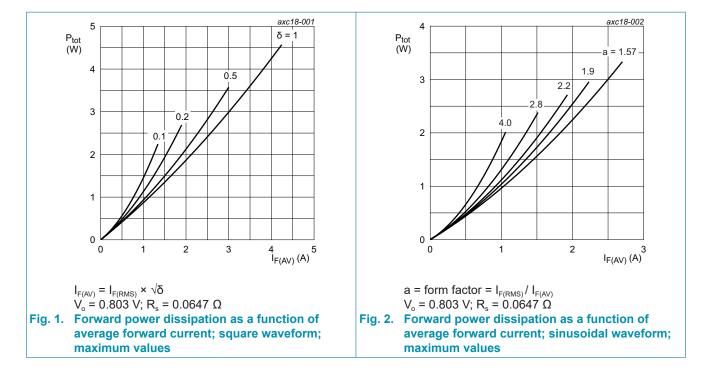
Table 4. Marking codes					
Type number	Marking codes				
MURS360B	360B				

8. Limiting values

Table 5. Limiting values

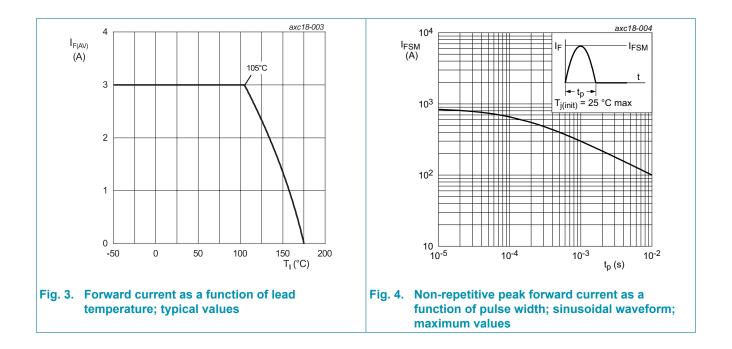
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{lead} ≤ 105 °C; Fig. 1; Fig. 2; Fig. 3	3	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{lead} ≤ 105 °C; square-wave pulse	6	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	110	A
T _{stg}	storage temperature		-65 to 175	°C
Tj	junction temperature		175	°C



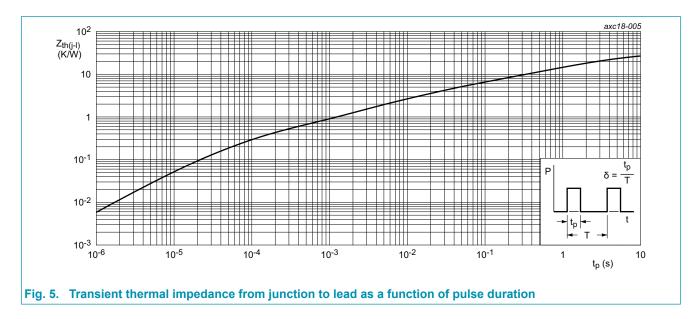
Ultrafast power diode

MURS360B



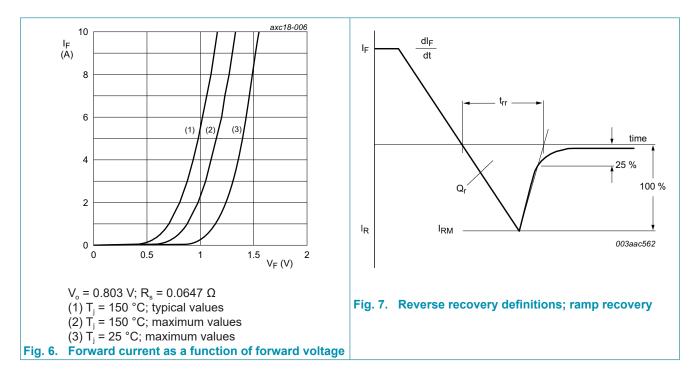
9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	mounted on a minimum footprint printed-circuit board (FR4); <u>Fig. 5</u>	-	23	25	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	mounted on a minimum footprint printed-circuit board (FR4)	-	75	-	K/W

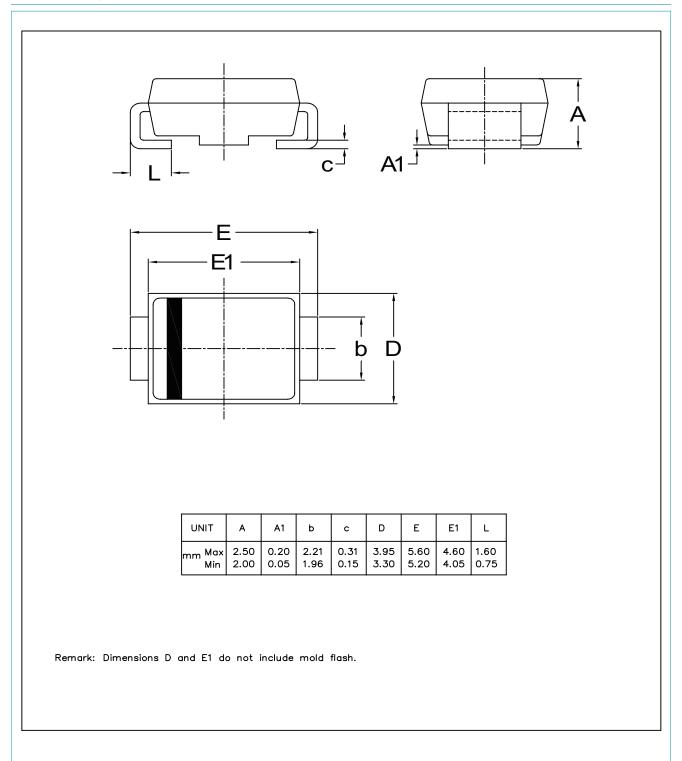


10. Characteristics

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
Static cha	racteristics	1	·		1		-
V _F	forward current	I _F = 3 A; T _j = 25 °C; <u>Fig. 6</u>	-		-	1.3	V
		I _F = 3 A; T _j = 150 °C; <u>Fig. 6</u>	-		0.88	1.05	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-		-	3	μA
		V _R = 600 V; T _j = 150 °C	-		-	1	mA
Dynamic	characteristics		·				
Q _r rev	reverse charge	$I_F = 3 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-		122	-	nC
		I _F = 3 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-		199	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-		50	-	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ Step recovery}$	-		-	50	ns
		$I_F = 3 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-		52	-	ns
		I _F = 3 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-		65	-	ns
I _{RM}	peak reverse recovery current	I _F = 3 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-		4.7	-	A
		I _F = 3 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-		6.1	-	A
E _{as}	non-repetitive avalanche energy	I _R = 1.2 A; T _{j(init)} = 25 °C; L = 15 mH	1	0.8	-	-	mJ



11. Package outline



MURS360B

Ultrafast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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13. Contents

1. (General description	1
2. I	Features and benefits	1
3. /	Applications	1
4. (Quick reference data	1
5. I	Pinning information	2
6. (Ordering information	2
7. I	Marking	2
8. I	Limiting values	3
9. '	Thermal characteristics	5
10.	Characteristics	6
11.	Package outline	7
12.	Legal information	8
13.	Contents1	0

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